AMENDMENTS TO THE CLAIMS

1. (Currently Amended) An X-ray exposure apparatus comprising:

two [[an]] X-ray mirrors containing a material having an absorption edge only in a range of a wavelength region other than 0.45 nm through 0.7 nm for as to X-rays, to provide light at least having a component in wavelength ranging from 0.45 nm through 0.7 nm, and

the x-ray mirror emanates an X-ray having a peaked wavelength in a range from 0.45 nm to 0.7 nm, wherein

the material having an absorption edge only in a wavelength region other than 0.45 nm through 0.7 nm is disposed at an outermost surface of the X-ray mirror, and

said X-ray mirrors receiving an X-ray having an angle of oblique angle of the X-ray with respect to the X-ray mirror is not incidence of no more than 1.5° thereby providing the light at least having a component in wavelength ranging from 0.45 nm through 0.7 nm, wherein

a first of said X-ray mirrors collects an X-ray outgoing from said X-ray mirrors, and
a second of said X-ray mirrors increases an area of a region illuminable by X-rays
outgoing from said X-ray mirrors.

2. (Original) The X-ray exposure apparatus according to claim 1, wherein said X-rays are included in radiation outgoing from a synchrotron radiation source.

Claim 3 (Cancelled)

4. (Currently Amended) The X-ray exposure apparatus according to claim 1, wherein said X-ray mirror contains mirrors contain a single type of mirror material selected from a group consisting of beryllium, titanium, silver, ruthenium, rhodium and palladium, nitrides, carbides and borides of these, diamond, diamond-like carbon and boron nitride.

Claims 5-10 (Cancelled)

11. (Original) The X-ray exposure apparatus according to claim 1 further comprising an X-ray mask, wherein said X-ray mask includes a membrane and an X-ray absorber formed on said membrane, and

said membrane contains a single species selected from a group consisting of diamond, diamond-like carbon, boron nitride and beryllium.

12. (Original) The X-ray exposure apparatus according to claim 1 further comprising an X-ray mask, wherein said X-ray mask includes a membrane and an X-ray absorber formed on said membrane,

said membrane contains a material having an absorption edge only in at least either one of a wavelength region of less than 0.45 nm and a wavelength region exceeding 0.7 nm as to X-rays, and

said X-ray absorber contains a material having an absorption edge in a wavelength region of at least 0.6 nm and less than 0.85 nm.

Claims 13-23 (Cancelled)

24. (Currently Amended) An X-ray exposure method comprising:

an X-ray incidence step of making X-rays incident upon [[an]] two X-ray mirrors containing a material having an absorption edge only in a range of wavelength region other than 0.45 nm through 0.7 nm for as to X-rays, said X-ray mirrors receiving an X-ray having an angle of oblique incidence on more than 15°; and

an exposure step of performing exposure with X-rays outgoing from said X-ray mirrors and at least having a component in wavelength ranging from 0.45 nm through 0.7 nm, wherein and

the x-ray mirror emanates an X-ray having a peaked wavelength in a range from 0.45 nm to 0.7 nm by setting an oblique angle of the X-ray with respect to the X-ray mirror to be not more than 1.5°, wherein

the material having an absorption edge only in a wavelength region other than 0.45 nm through 0.7 nm is disposed at an outermost surface of the X-ray mirror

a first of said X-ray mirrors collects an X-ray outgoing from said X-ray mirrors, and
a second of said X-ray mirrors increases an area of a region illuminable by X-rays
outgoing from said X-ray mirrors.

25. (Original) The X-ray exposure method according to claim 24, further comprising an X-ray outgoing step of making said X-rays outgo from a synchrotron radiation source.

Claim 26 (Cancelled)

27. (Currently Amended) The X-ray exposure method according to claim 24, wherein said X-ray mirror contains mirrors contain a single type of mirror material selected from a group consisting of beryllium, titanium, silver, ruthenium, rhodium and palladium, nitrides, carbides and borides of these, diamond, diamond-like carbon and boron nitride.

Claims 28-33 (Cancelled)

34. (Original) The X-ray exposure method according to claim 24 employing an X-ray mask, wherein said X-ray mask includes a membrane and an X-ray absorber formed on said membrane, and

said membrane contains a single species selected from a group consisting of diamond, diamond-like carbon, boron nitride and beryllium.

35. (Original) The X-ray exposure method according to claim 24 employing an X-ray mask, wherein said X-ray mask includes a membrane and an X-ray absorber formed on said membrane,

said membrane contains a material having an absorption edge only in at least either one of a wavelength region of less than 0.45 nm and a wavelength region exceeding 0.7 nm as to X-rays, and

said X-ray absorber contains a material having an absorption edge in a wavelength region of at least 0.6 nm and less than 0.85 nm.

Claims 36-38 (Cancelled)

39. (Original) A semiconductor device manufactured with the X-ray exposure method according to claim 24.

40. (Currently Amended) A synchrotron radiation apparatus comprising a synchrotron radiation source and [[an]] two X-ray mirror group including a plurality of X-ray mirrors upon which radiation outgoing from said synchrotron radiation source is incident, wherein

said two X-ray mirrors containing a material having an absorption edge only in a range of wavelength region other than 0.45 nm through 0.7 nm for as to X-rays, and receiving an X-ray having an angle of oblique incidence on more than 15°,[[;]]

the outgoing direction of said radiation outgoing from said synchrotron radiation source and the outgoing direction of reflected light outgoing from said X-ray mirror group are substantially identical,

said X-ray mirror provides light at least having a component in wavelength ranging from 0.45nm through 0.7 nm, and

the X-ray mirror emanates an X-ray having a peaked wavelength in a range from 0.45 nm to 0.7 nm, wherein

the material having an absorption edge only in a wavelength region other than 0.45 nm through 0.7 nm is disposed at an outermost surface of the X-ray mirror, and

an oblique angle of the X-ray with respect to the X-ray mirror is not more than 1.5° thereby providing the light at least having a component in wavelength ranging from 0.45 nm through 0.7 nm

a first of said X-ray mirrors collects an X-ray outgoing from said X-ray mirrors, and

a second of said X-ray mirrors increases an area of a region illuminable by X-rays outgoing from said X-ray mirrors.

Claim 41 (Cancelled)

42. (Currently Amended) A synchrotron radiation method employing a synchrotron radiation apparatus emprising including a synchrotron radiation source and an X-ray mirror group including a plurality of two X-ray mirrors upon which radiation outgoing from said synchrotron radiation source is incident, said two X-ray mirrors containing a material having an absorption edge only in a range of a wavelength other than 0.45 nm through 0.7 nm for X-rays, the synchrotron radiation method comprising:

a radiation incidence step of making radiation outgoing from the synchrotron radiation source incident upon [[an]] said two X-ray mirrors an X-ray outgoing from the synchrotron radiation source and having an angle of oblique incidence of no more than 1.5°; containing a material having an absorption edge only in a wavelength region other than 0.45 nm through 0.7 nm as to X-rays, and

an exposure step of performing exposure with X-rays outgoing from said X-ray mirrors, wherein

a reflected light emitting step of emitting reflected light from said X-ray mirror group in a direction substantially identical to the outgoing direction of the radiation outgoing from said synchrotron radiation source, said reflected light at least having a component in wavelength ranging from 0.45 nm through 0.7 nm, and

the x-ray mirror emanates an X-ray having a peaked wavelength in a range from 0.45 nm to 0.7 nm by setting an oblique angle of the X-ray with respect to the X-ray mirror to be not more than 1.5°, wherein

the material having an absorption edge only in a wavelength region other than 0.45 nm through 0.7 nm is disposed at an outermost surface of the X-ray mirror

a first of said X-ray mirrors collects an X-ray outgoing from said X-ray mirrors, and
a second of said X-ray mirrors increases an area of a region illuminable by X-rays
outgoing from said X-ray mirrors.

Claims 43-45 (Cancelled)

- 46. (Currently Amended) The X-ray exposure apparatus of claim 1, further comprising means altering a peak wavelength of said light emanating from said X ray mirror mirrors while maintaining a direction of said light emanating from said X ray mirror mirrors.
- 47. (Currently Amended) The X-ray exposure apparatus of claim 1, further comprising means altering a peak wavelength of said light emanating from said X-ray mirror mirrors while maintaining an optical axis of said light emanating from said X-ray mirror mirrors.
- 48. (Currently Amended) The X-ray exposure method of claim 24, further comprising the step of altering a peak wavelength of said X-ray emanating from said X-ray mirrors while maintaining a direction of said X-ray emanating from said X-ray mirrors.

49. (Currently Amended) The X-ray exposure method of claim 24, further comprising the step of altering a peak wavelength of said X-ray emanating from said X-ray mirrors while maintaining an optical axis of said X-ray emanating from said X-ray mirrors.

50. (New) An X-ray exposure apparatus, comprising:

a first stage X-ray mirror, and

a second stage X-ray mirror, wherein

α represents an angle of oblique incidence of an X-ray incident on said first stage X-ray mirror and said second stage X-ray mirror,

L represents a distance between said first and second stage X-ray mirrors, as seen along an x-axis corresponding to a direction of the X-ray incident on said first stage X-ray mirror,

D represents a distance from incidence of an optical axis of the X-ray incident on said first stage X-ray mirror to said second stage X-ray mirror, and

said α and L are changed to satisfy a relationship D = L x tan (2 α), whereby respective optical axes of X-rays have substantially identical directions, and a spectral distribution of an X-ray outgoing from said second stage is changed.

51. (New) An X-ray exposure apparatus. comprising:

a first stage X-ray mirror,

a second stage X-ray mirror, and

a third stage X-ray mirror, wherein

α represents an angle of oblique incidence of an X-ray incident on said first stage X-ray mirror and said third stage X-ray mirror,

 2α represents an angle of oblique incidence of an X-ray incident on said second stage X-ray mirror,

L represents a distance between said first and second stage X-ray mirrors and a distance between said second and third stage X-ray mirrors, as seen along an x-axis corresponding to a direction of the X-ray incident on said first stage X-ray mirror,

D represents a distance from incidence of an optical axis of the X-ray incident on said first stage X-ray mirror to said second stage X-ray mirror, and

said α and L are changed to satisfy a relationship D = L x tan (2 α), whereby respective optical axes of X-rays have substantially identical directions, and a spectral distribution of an X-ray outgoing from said third stage is changed.

52. (New) An X-ray exposure apparatus, comprising:

a first stage X-ray mirror,

a second stage X-ray mirror,

a third stage X-ray mirror, and

a fourth stage X-ray mirror, wherein

α represents an angle of oblique incidence of an X-ray incident on each of said first, second, third and fourth stage X-ray mirrors,

L represents a distance between said first and second stage X-ray mirrors and a distance between said third and fourth stage X-ray mirrors, as seen along an x-axis corresponding to a direction of the X-ray incident on said first stage X-ray mirror,

D represents a distance from incidence of an optical axis of the X-ray incident on said first stage X-ray mirror to said third and fourth stage X-ray mirrors, and

said α and L are changed to satisfy a relationship D = L x tan (2 α), whereby respective optical axes of X-rays have substantially identical directions, and a spectral distribution of an X-ray outgoing from said fourth stage is changed.

- 53. (New) An X-ray exposure apparatus, comprising:
- a first stage X-ray mirror,
- a second stage X-ray mirror,
- a third stage X-ray mirror, and
- a fourth stage X-ray mirror, wherein

 α represents an angle of oblique incidence of an X-ray incident on each of said first and fourth stage X-ray mirrors,

 β represents and angle of oblique incidence of an X-ray incident on each of said second and third stage X-ray mirrors,

Lα represents a distance between said first and second stage X-ray mirrors and a distance between said third and fourth stage X-ray mirrors, as seen along an x-axis corresponding to a direction of the X-ray incident on said first stage X-ray mirror,

Lβ represents a distance between said second and third stage X-ray mirrors, as seen along said x-axis,

D represents a distance between said second and third stage X-ray mirrors, as seen along a y-axis corresponding to a direction perpendicular to said x-axis, and

said α , β , $L\alpha$ and $L\beta$ are changed to satisfy a relationship $D = 2 \times L\alpha \times \tan(2\alpha) =$

 $L\beta$ x tan(β-α), whereby

respective optical axes of X-rays have substantially identical directions, and

a spectral distribution of an X-ray outgoing from said fourth stage is changed.